

**PNP Epitaxial Planar High Current (High Performance) Transistor**

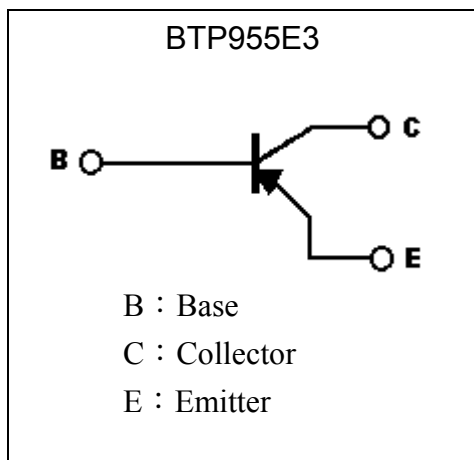
# BTP955E3

$BV_{CEO}$	-140V
$I_C$	-5A
$R_{CE(SAT)}$	90mΩ typ.

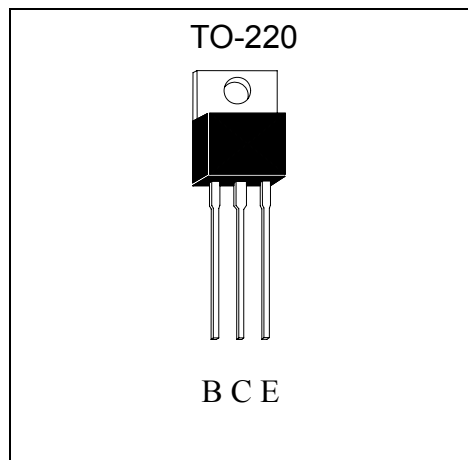
## Features

- 5 Amps continuous current, up to 10 Amps peak current
- Very low saturation voltage
- Excellent gain characteristics specified up to 3 Amps
- Extremely low equivalent on resistance,  $R_{CE(SAT)}=90m\Omega$  at 3A
- RoHS compliant package

## Symbol

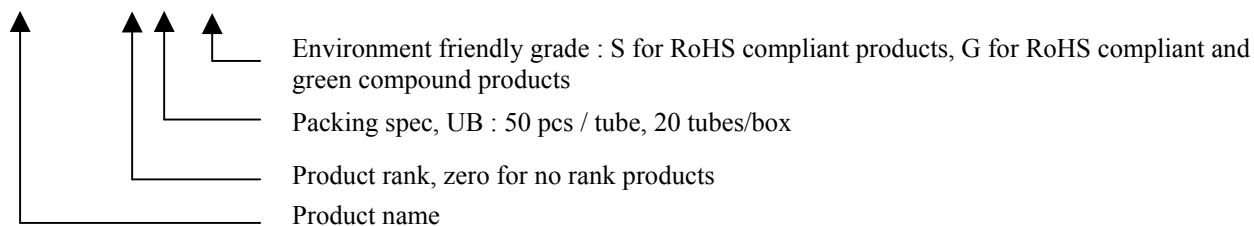


## Outline



## Ordering Information

Device	Package	Shipping
BTP955E3-0-UB-G	TO-220 (Pb-free lead plating)	50 pcs / tube, 20 tubes/ box , 4 boxes/carton





**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-140	
Emitter-Base Voltage	V <sub>EBO</sub>	-6	
Continuous Collector Current	I <sub>C</sub>	-5	A
Peak Collector Current	I <sub>CP</sub>	-10 (Note 1)	
Base Current	I <sub>B</sub>	-1	
Power Dissipation @T <sub>A</sub> =25°C	P <sub>D</sub>	2	W
Power Dissipation @T <sub>C</sub> =25°C		31	
Operating and Storage Temperature Range	T <sub>j</sub> ; T <sub>stg</sub>	-55 ~ +150	°C

Note: 1.Single pulse, Pw≤10ms

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	62.5	°C/W
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	4	

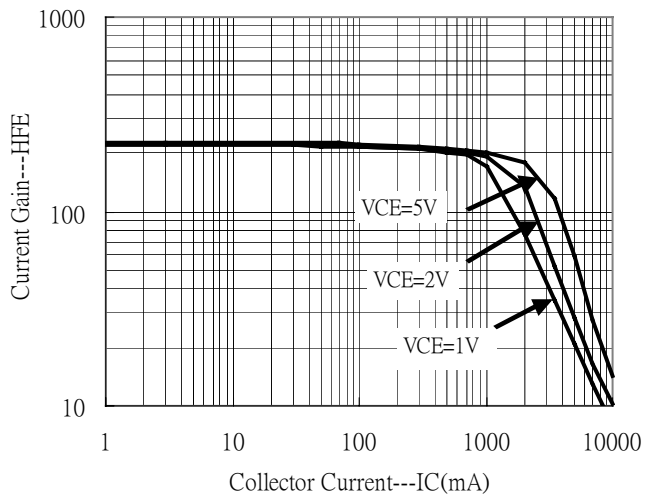
**Characteristics** (Ta=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	-180	-210	-	V	I <sub>C</sub> =-100μA
*BV <sub>CEO</sub>	-140	-170	-		I <sub>C</sub> =-10mA
BV <sub>EBO</sub>	-6	-8	-		I <sub>E</sub> =-100μA
I <sub>CBO</sub>	-	-	-50	nA	V <sub>CB</sub> =-150V
I <sub>EBO</sub>	-	-	-10		V <sub>EB</sub> =-6V
*V <sub>CE(sat)1</sub>	-	-40	-60	mV	I <sub>C</sub> =-100mA, I <sub>B</sub> =-5mA
*V <sub>CE(sat)2</sub>	-	-70	-120		I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA
*V <sub>CE(sat)3</sub>	-	-110	-150		I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA
*V <sub>CE(sat)4</sub>	-	-270	-370		I <sub>C</sub> =-3A, I <sub>B</sub> =-300mA
*V <sub>BE(sat)</sub>	-	-930	-1110		I <sub>C</sub> =-3A, I <sub>B</sub> =-300mA
*V <sub>BE(on)</sub>	-	-830	-950		V <sub>CE</sub> =-5V, I <sub>C</sub> =-3A
R <sub>CE(sat)</sub>	-	90	123	mΩ	I <sub>C</sub> =-3A, I <sub>B</sub> =-300mA
h <sub>FE1</sub>	100	200	-	-	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA
*h <sub>FE2</sub>	150	200	400	-	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A
*h <sub>FE3</sub>	75	140	-	-	V <sub>CE</sub> =-5V, I <sub>C</sub> =-3A
*h <sub>FE4</sub>	-	10	-	-	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10A
f <sub>T</sub>	-	110	-	MHz	V <sub>CE</sub> =-10V, I <sub>C</sub> =-100mA, f=50MHz
C <sub>ob</sub>	-	40	-	pF	V <sub>CB</sub> =-20V, f=1MHz

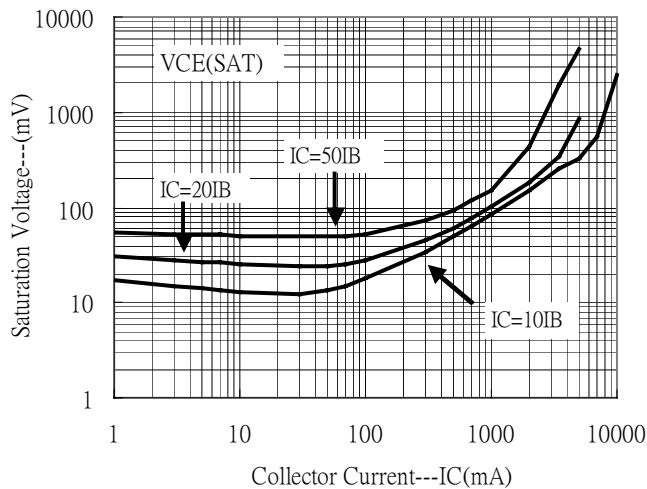
\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

**Typical Characteristics**

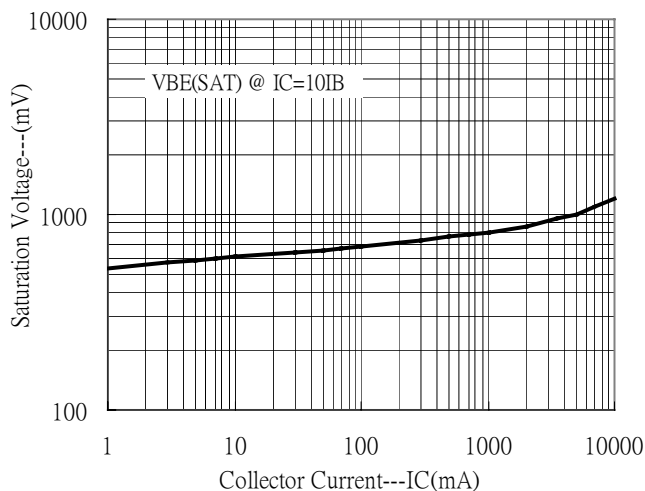
Current Gain vs Collector Current



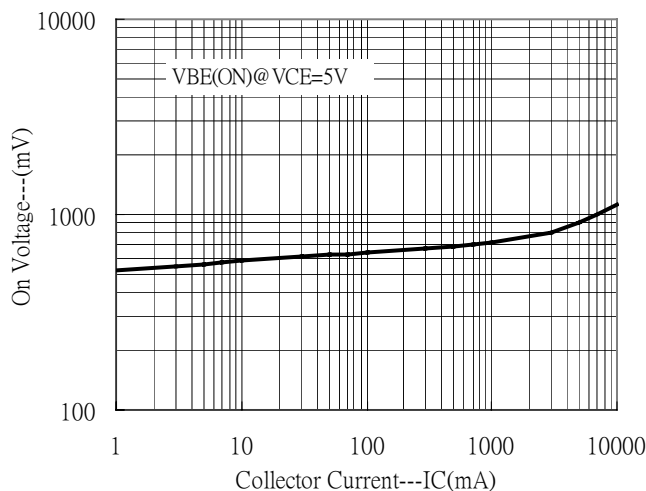
Saturation Voltage vs Collector Current



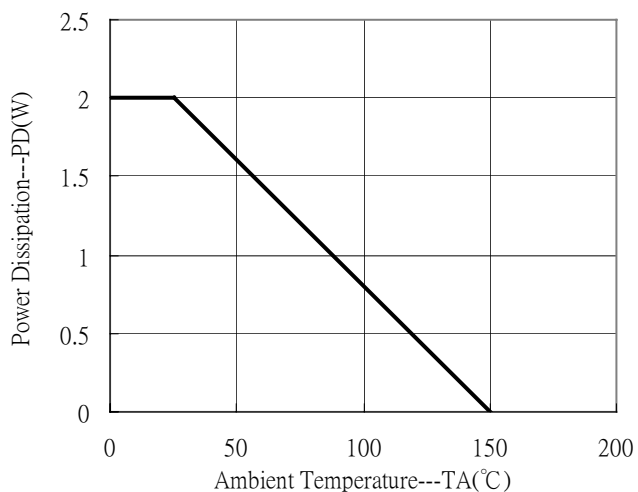
Saturation Voltage vs Collector Current



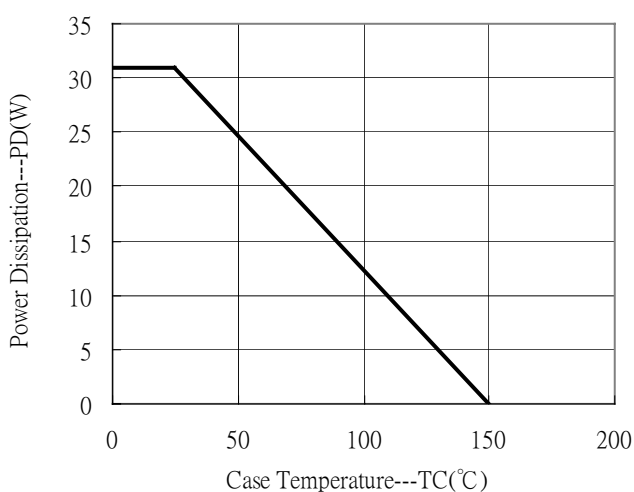
On Voltage vs Collector Current



Power Derating Curve



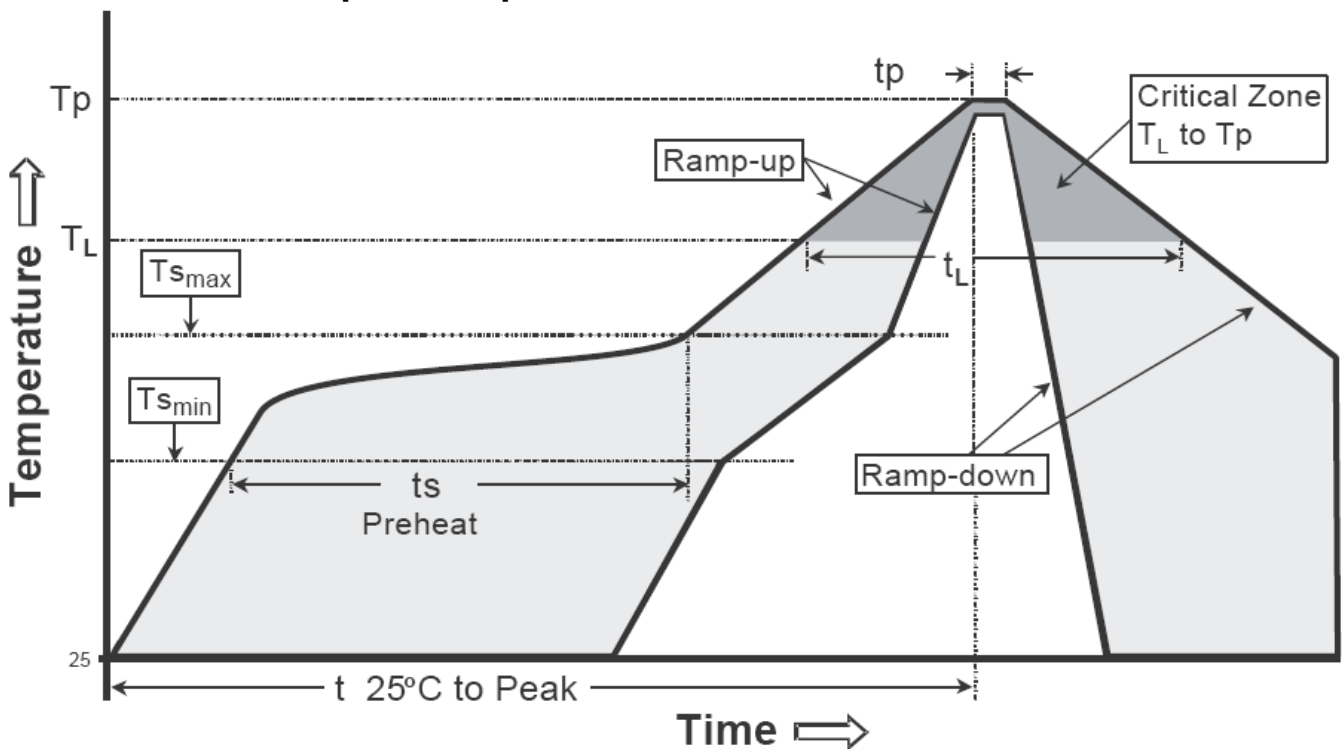
Power Derating Curve



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

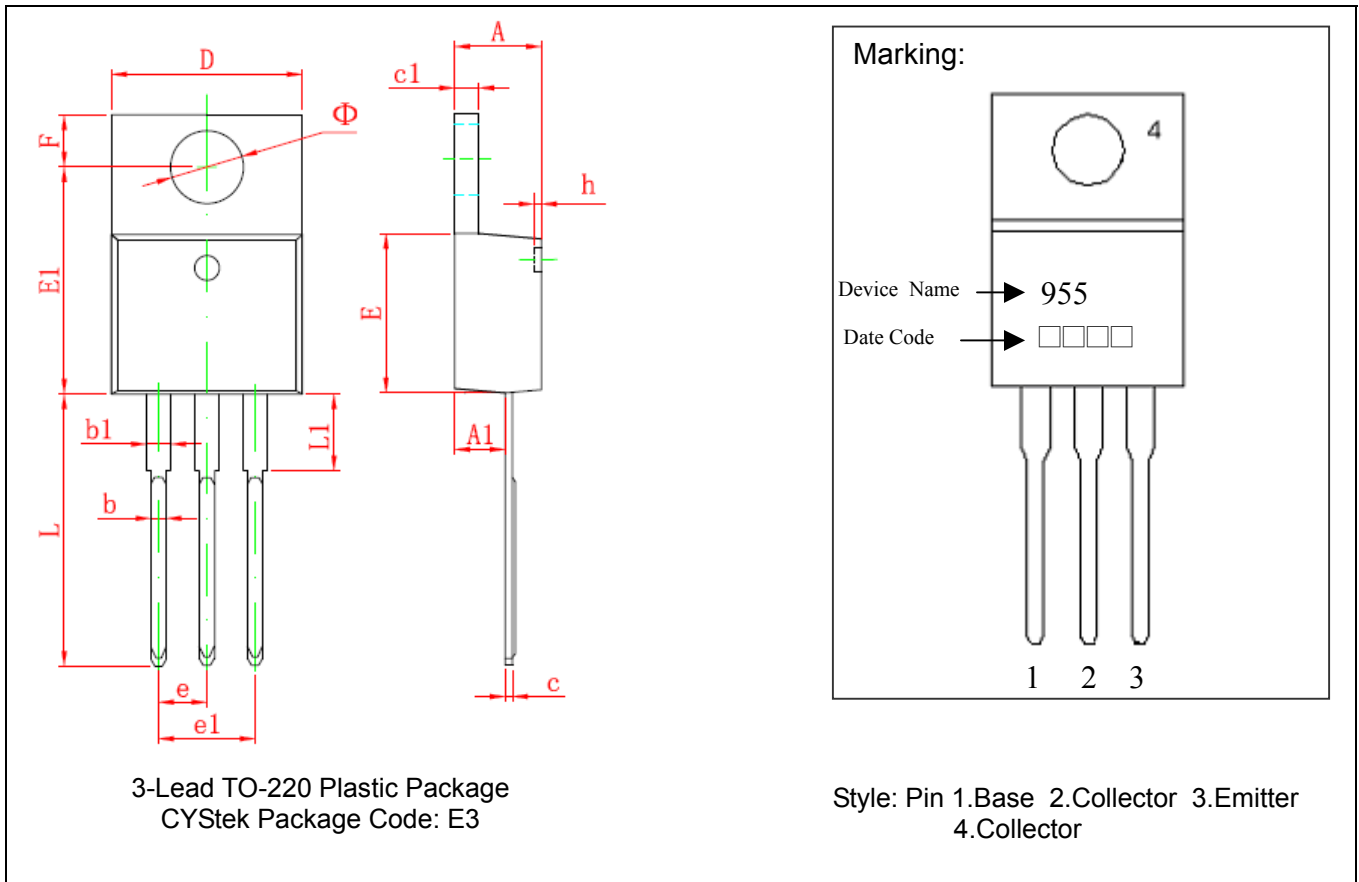
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>P</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**TO-220 Dimension**



**3-Lead TO-220 Plastic Package**  
 CYStek Package Code: E3

**Marking:**

Device Name → 955  
 Date Code → □□□□

Style: Pin 1.Base 2.Collector 3.Emitter  
 4.Collector

\*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184	E1	12.060	12.460	0.475	0.491
A1	2.520	2.820	0.099	0.111	e	2.540*		0.100*	
b	0.710	0.910	0.028	0.036	e1	4.980	5.180	0.196	0.204
b1	1.170	1.370	0.046	0.054	F	2.590	2.890	0.102	0.114
c	0.310	0.530	0.012	0.021	h	0.000	0.300	0.000	0.012
c1	1.170	1.370	0.046	0.054	L	13.400	13.800	0.528	0.543
D	10.010	10.310	0.394	0.406	L1	3.560	3.960	0.140	0.156
E	8.500	8.900	0.335	0.350	Φ	3.735	3.935	0.147	0.155

**Notes:** 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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